

NPN SWITCHING SILICON TRANSISTOR

Qualified per MIL-PRF-19500/251

Devices

2N2218	2N2219
2N2218A	2N2219A
2N2218AL	2N2219AL

Qualified Level

JAN
JANTX
JANTXV
JANS

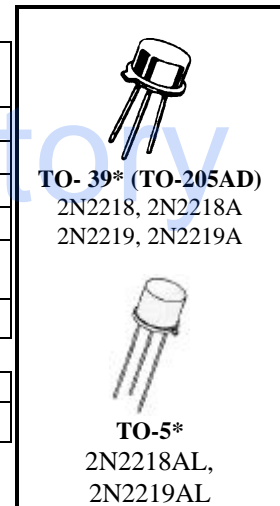
MAXIMUM RATINGS

Ratings	Symbol	2N2218 2N2219	2N2218A; L 2N2219A; L	Unit
Collector-Emitter Voltage	V_{CEO}	30	50	Vdc
Collector-Base Voltage	V_{CBO}	60	75	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	6.0	Vdc
Collector Current	I_C	800		mAdc
Total Power Dissipation	P_T	@ $T_A = +25^{\circ}\text{C}^{(1)}$	0.8	W
		@ $T_C = +25^{\circ}\text{C}^{(2)}$	3.0	W
Operating & Storage Junction Temp. Range	T_{op}, T_{stg}	-55 to +200		$^{\circ}\text{C}$

THERMAL CHARACTERISTICS

Characteristics	Symbol	Max.	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	59	$^{\circ}\text{C}/\text{W}$

- 1) Derate linearly 4.6 mW/ $^{\circ}\text{C}$ above $T_A > +25^{\circ}\text{C}$
 2) Derate linearly 17.0 mW/ $^{\circ}\text{C}$ above $T_C > +25^{\circ}\text{C}$



*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_E = 10 \text{ mAdc}$	2N2218; 2N2219 2N2218A; L; 2N2219A; L	$V_{(BR)CEO}$	30 50	Vdc
Emitter-Base Cutoff Current $V_{EB} = 5.0 \text{ Vdc}$ $V_{EB} = 6.0 \text{ Vdc}$ $V_{EB} = 4.0 \text{ Vdc}$	2N2218; 2N2219 2N2218A; L; 2N2219A; L All Types	I_{EBO}	10 10 10	μAdc ηAdc
Collector-Base Cutoff Current $V_{CE} = 30 \text{ Vdc}$ $V_{CE} = 50 \text{ Vdc}$	2N2218; 2N2219 2N2218A; L; 2N2219A; L	I_{CES}	10 10	ηAdc

2N2218; A; AL; 2N2219; A; AL JAN SERIES

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
Collector-Base Cutoff Current				
$V_{CB} = 50$ Vdc 2N2218; 2N2219	I_{CBO}		10	η Adc
$V_{CB} = 60$ Vdc 2N2218A; L; 2N2219A; L			10	
$V_{CB} = 60$ Vdc 2N2218; 2N2219			10	μ Adc
$V_{CB} = 75$ Vdc 2N2218A; L; 2N2219A; L			10	

ON CHARACTERISTICS (3)

Forward-Current Transfer Ratio					
$I_C = 0.1$ mAdc, $V_{CE} = 10$ Vdc 2N2218 2N2219	h_{FE}		20 35		
$I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc 2N2218A; 2N2218AL 2N2219A; 2N2219AL			30 50		
			25 50	150 325	
$I_C = 10$ mAdc, $V_{CE} = 10$ Vdc 2N2218 2N2219			35 75	150 325	
			35 75		
$I_C = 150$ mAdc, $V_{CE} = 10$ Vdc 2N2218A; 2N2218AL 2N2219A; 2N2219AL			40 100		
			40 100	120 300	
$I_C = 500$ mAdc, $V_{CE} = 10$ Vdc 2N2218; A; 2N2218AL 2N2219; A; 2N2219AL			20 30		
			20 30		
Collector-Emitter Saturation Voltage					
$I_C = 150$ mAdc, $I_B = 15$ mAdc 2N2218; 2N2219		$V_{CE(sat)}$		0.4 0.3	Vdc
$I_C = 500$ mAdc, $I_B = 50$ mAdc 2N2218A; L; 2N2219A; L				1.6 1.0	
Base-Emitter Saturation Voltage					
$I_C = 150$ mAdc, $I_B = 15$ mAdc 2N2218; 2N2219	$V_{BE(sat)}$		0.6 0.6	Vdc	
$I_C = 500$ mAdc, $I_B = 50$ mAdc 2N2218A; L; 2N2219A, L			1.2 2.6 2.0		

DYNAMIC CHARACTERISTICS

Magnitude of Small-Signal Forward Current Transfer Ratio $I_C = 20$ mAdc, $V_{CE} = 20$ Vdc, $f = 100$ MHz	$ h_{fe} $	2.5	12	
Small-Signal Forward Current Transfer Ratio $I_C = 1.0$ mAdc, $V_{CE} = 10$ Vdc, $f = 1.0$ kHz	h_{fe}	25		
2N2218		50		
2N2219		35		
2N2218A, L 2N2219A, L		75		
Output Capacitance $V_{CB} = 10$ Vdc, $I_E = 0$, 100 kHz $\leq f \leq 1.0$ MHz	C_{obo}		8.0	pF
Input Capacitance $V_{EB} = 0.5$ Vdc, $I_C = 0$, 100 kHz $\leq f \leq 1.0$ MHz	C_{ibo}		25	pF

SWITCHING CHARACTERISTICS

$V_{CC} = 30$ Vdc; $I_C = 150$ mAdc; $I_{B1} = 15$ mAdc

Turn-On Time (See Figure 3 of MIL-PRF-19500/251)	2N2218, 2N2219 2N2218A, L, 2N2219A, L	t_{on}	40 35	η s
Turn-Off Time (See Figure 4 of MIL-PRF-19500/251)	2N2218, 2N2219 2N2218A, L, 2N2219A, L		250 300	

(3) Pulse Test: Pulse Width = 300 μ s, Duty Cycle $\leq 2.0\%$.